

**Changes to the Specification**

Please replace paragraph [0015] with the following amended paragraph:

[0015] Referring to FIG. 2a, a CMOS image sensor 9 is formed on an epitaxial wafer 10 having a structure formed by an epitaxial layer 12 doped with a low concentration and positioned on a p-type or n-type substrate 11 doped with a high concentration. An active area is isolated from other active areas by ~~[[a]]~~ an STI layer 13.